

Silicon NPN Power Transistor

BU603

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
 : $V_{CEO(SUS)} = 550V(\text{Min})$
- High Switching Speed

APPLICATIONS

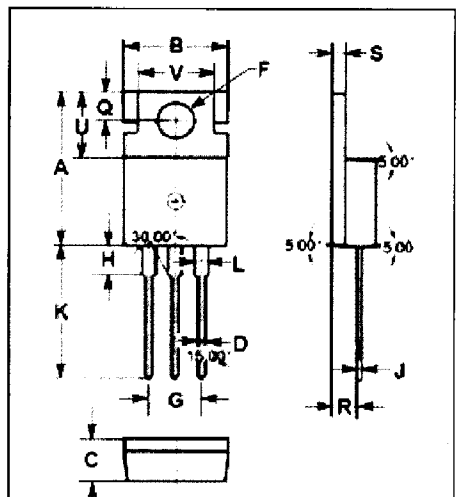
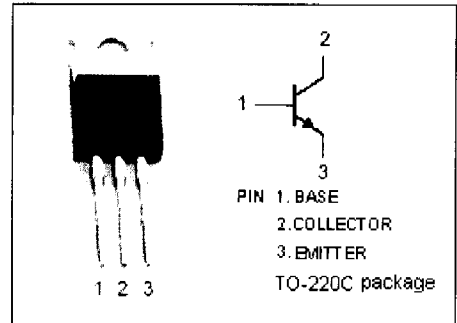
- Designed for use in power supplies and deflection circuits for color receivers and monitors

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

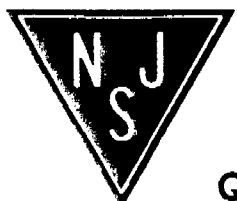
SYMBOL	PARAMETER	VALUE	UNIT
V_{CES}	Collector-Emitter Voltage- $V_{BE} = 0$	1350	V
V_{CEO}	Collector-Emitter Voltage	550	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	5	A
I_{CM}	Collector Current-Peak	8	A
I_B	Base Current-Continuous	2	A
I_{BM}	Base Current-Peak	4	A
I_E	Emitter Current-Continuous	7	A
I_{EM}	Emitter Current-Peak	12	A
P_C	Collector Power Dissipation $T_C=25^\circ\text{C}$	100	W
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.25	$^\circ\text{C/W}$



DIM	mm	
	MIN	MAX
A	15.70	15.90
B	9.90	10.10
C	4.20	4.40
D	0.70	0.90
F	3.40	3.60
G	4.98	5.18
H	2.70	2.90
J	0.44	0.46
K	13.20	13.40
L	1.10	1.30
Q	2.70	2.90
R	2.50	2.70
S	1.29	1.31
U	6.45	6.65
V	8.66	8.86



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Quality Semi-Conductors

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ELECTRICAL CHARACTERISTICS

$T_c=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE0(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=100\text{mA}; I_B=0$	550			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C=2\text{A}; I_B=0.33\text{A}$			2	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C=4\text{A}; I_B=1.33\text{A}$			3	V
I_{CES}	Collector Cutoff Current	$V_{CE}=V_{CESmax}; V_{BE}=0$ $V_{CE}=V_{CESmax}; V_{BE}=0; T_J=125^\circ\text{C}$			1 2	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=6\text{V}; I_C=0$			1	mA
h_{FE-1}	DC Current Gain	$I_C=10\text{mA}; V_{CE}=5\text{V}$	6			
h_{FE-2}	DC Current Gain	$I_C=1\text{A}; V_{CE}=5\text{V}$	8			
h_{FE-3}	DC Current Gain	$I_C=2\text{A}; V_{CE}=2\text{V}$	6			
h_{FE-4}	DC Current Gain	$I_C=4\text{A}; V_{CE}=3\text{V}$	3			

Switching Times; Resistive Load

t_{on}	Turn-On Time	$I_C=2\text{A}; I_{B1}=-I_{B2}=0.33\text{A}$			0.5	μs
t_s	Storage Time				6.0	μs
t_f	Fall Time				0.7	μs